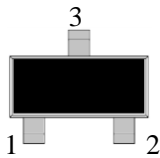
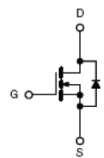


## 1、Features

- High dense cell design for extremely low RDS(ON)
- Exceptional on-resistance and maximum DC current capability
- Load/Power Switching
- Interfacing Switching

## 2、Pinning information

PIN	Description	Simplified outline	
1	GATE(G)		
2	SOURCE(S)		
3	DRAIN(D)		

## 3、Limiting value

(Ta = 25°C unless otherwise noted).

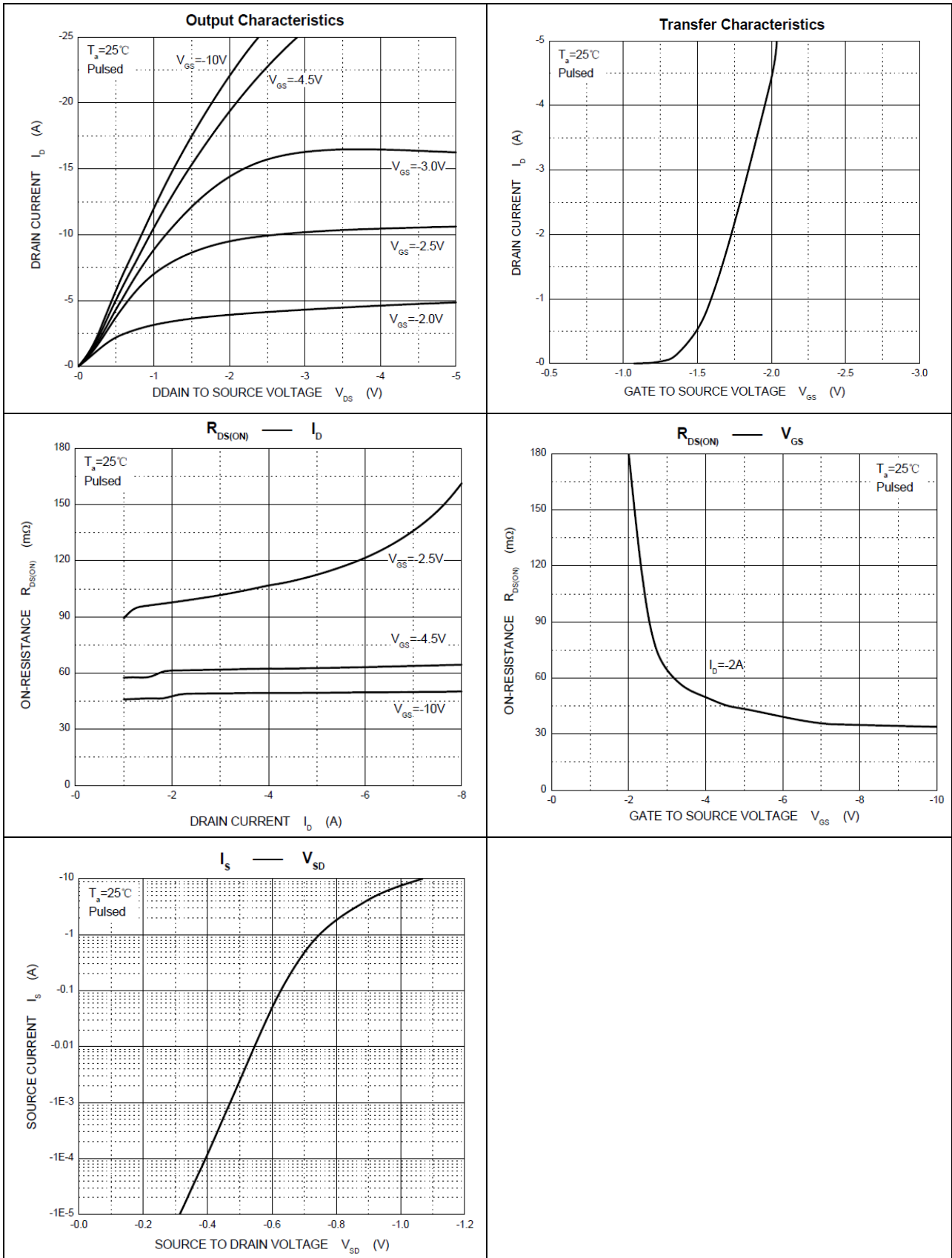
SYMBOL	PARAMETER	Limit	UNIT
Vds	Drain-Source Voltage	-30	V
Vgs	Gate-Source Voltage	±12	V
Id	Continuous Drain Current	-4.2	A
Pd	Power Dissipation	350	mW
RθJA	Thermal Resistance from Junction to Ambient	357	°C/W
Tj	Operating Junction Temperature	+150	°C
Tstg	Operating Junction and Storage Temperature Range	-50 to +150	°C

## 4、Electrical Characteristics (Ta = 25°C unless otherwise noted)

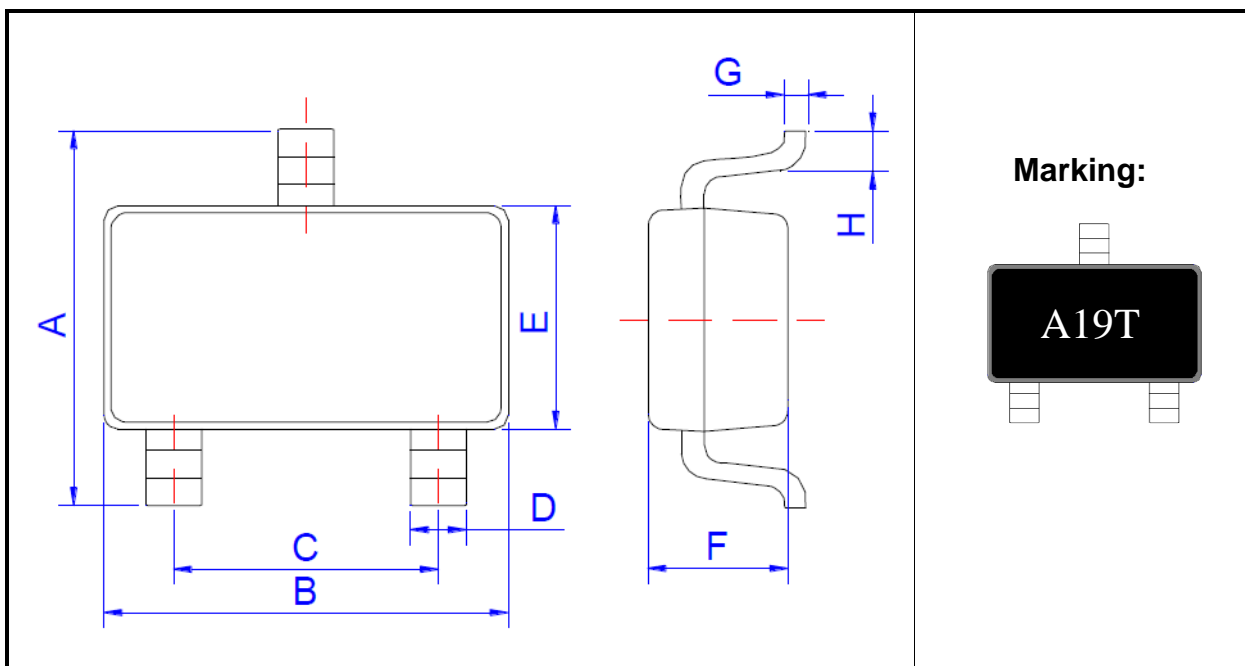
SYMBOL	PARAMETER	CONDITIONS	MIN	Typ	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	VGS=0 V, ID=-250 μA	-30			V
V <sub>th(GS)</sub>	Gate-Threshold Voltage	VDS=VGS, ID=-250 μA	-0.7		-1.3	V
I <sub>GSS</sub>	Gate-body Leakage	VDS=0 V, VGS=±12V			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	VDS=-24 VGS=0 V			-1	u
R <sub>DS(ON)</sub>	Drain-Source On-Resistance	VGS=-10 V, ID=-4.2A			65	mΩ
		VGS=-4.5 V, ID=-4A			75	
		VGS=-2.5 V, ID=-1A			90	
g <sub>fs</sub>	Forward Trans conductance	VDS=5V, ID=5A	7			S
V <sub>SD</sub>	Diode Forward Voltage	IS=-1A, VGS=0 V			-1.0	V
C <sub>iss</sub>	Input Capacitance*	VDS=-15V, VGS=0V, f=1MHz		954		pF
C <sub>oss</sub>	Output Capacitance*			115		pF
C <sub>rss</sub>	Reverse Transfer Capacitance*			77		pF
T <sub>d(on)</sub>	Turn-on Time*	VDS=-15V, VGS=-10V RL=3.6Ω, RG=6Ω			6.3	nS
T <sub>d(off)</sub>	Turn-off Time*				38.2	nS

\*These parameters have no way to verify.

5. Electrical Characteristics Curve



## 6、Package outline(SOT-23)



DIM	Inches			Milimeters		
	Min	Type	Max	Min	Type	Max
A	0.104		0.116	2.65		2.95
B		0.115			2.92	
C		0.075			1.90	
D	0.014		0.018	0.35		0.45
E		0.051			1.30	
F		0.043			1.10	
G		0.006			0.16	
H	0.010		0.022	0.25		0.55